

60HFU... SERIES

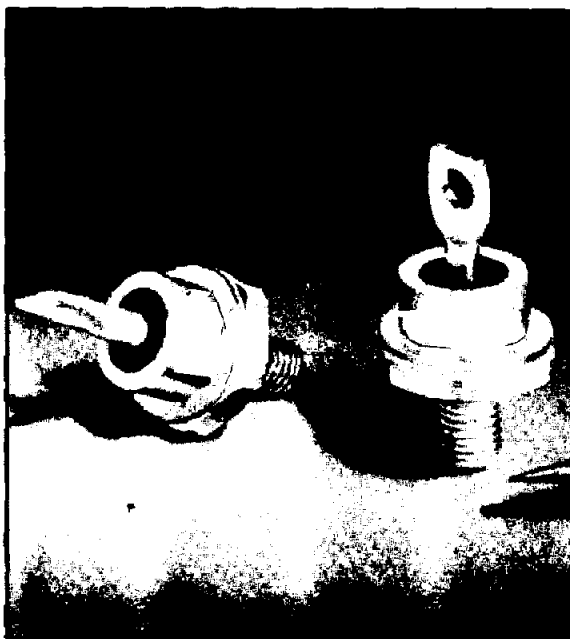
SUPER FAST RECTIFIER DIODE 60 Amp 60ns

Major ratings and characteristics

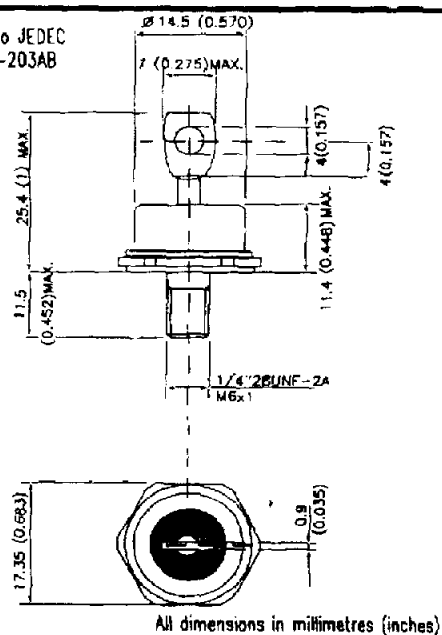
	60HFU	Units
$I_T(\text{AVG})$	60	A
T_c	82	°C
I_{RMS}	94	A
$I_{\text{FSM}} @ 10\text{ms}$	830	A
$I_{\text{FSM}} @ 8.3\text{ms}$	870	A
V_{RRM}	100 to 600	V
T_J	-40 to 125	°C

Description and Features

- Very low reverse recovery time
- Reduced switching losses
- Soft recovery characteristics
- High surge current capability
- No voltage derating up to 150°C
- Stud cathode and stud anode versions
- Designed for switching applications:
Free wheeling diode in converters and
control circuits
Rectifier in S.M.P.S.



Conforms to JEDEC
Outline DO-203AB
(DO-5)



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ELECTRICAL SPECIFICATIONS

Forward Conduction

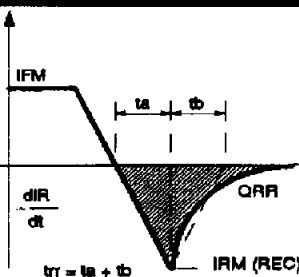
Parameters	Value	Units	Conditions
$I_{F(AV)}$ Maximum average forward current	60	A	180° conduction, half sine cond @ Case temperature = 82°C
	67	A	180° conduction, rect cond @ Case temperature = 82°C
I_{RMS} Maximum RMS current	94	A	
I_{SM} Maximum peak, one-cycle non-repetitive forward current Initial $T_J = T_J \text{ max.}$	830	A	$t = 10\text{ms}$ No voltage reapplied
	870	A	$t = 8.3\text{ms}$ No voltage reapplied
	700	A	$t = 10\text{ms}$ 100% V_{RM} reapplied
	730	A	$t = 8.3\text{ms}$ 100% V_{RM} reapplied
P_T Maximum P_T for fusing Initial $T_J = T_J \text{ max.}$	3460	A ² s	$t = 10\text{ms}$ No voltage reapplied
	3160	A ² s	$t = 8.3\text{ms}$ No voltage reapplied
	2450	A ² s	$t = 10\text{ms}$ 100% V_{RM} reapplied
	2240	A ² s	$t = 8.3\text{ms}$ 100% V_{RM} reapplied
P_{VT} Maximum P_{VT} for fusing	34600	A ² √s	$t = 0$ to 10ms, no voltage reapplied
$V_{F(TO)}$ Maximum value of threshold voltage	1.08	V	$T_J = 125^\circ\text{C}$
r_i Maximum value of forward slope resistance	3.40	mΩ	$T_J = 125^\circ\text{C}$
V_{FU} Maximum forward voltage drop	1.50	V	$I_{FM} = 60\text{ Apk}$ $T_J = 25^\circ\text{C}$
	1.30	V	$I_{FM} = 60\text{ Apk}$ $T_J = 125^\circ\text{C}$

Thermal and Mechanical Specifications

T_J Junction temperature range	-40 to 125	°C	
T_{stg} Storage temperature range	-40 to 150	°C	
$R_{\theta JC}$ Maximum thermal resistance, junction to case	0.36	K/W	DC operation per junction
$R_{\theta HS}$ Maximum thermal resistance, case to heatsink	0.25	K/W	Mounting surface, smooth and greased
T Mounting torque, base to heatsink $\pm 10\%$	2.5	Nm	A mounting compound is recommended and the torque should be rechecked after a period of about 3 hours to allow for the spread of the compound
wt Approximate weight	25	g	

Recovery Characteristics

Parameters	Typ.	Max.	Units	Conditions
t_{rr} Recovery time	60	80	ns	$T_J = 25^\circ\text{C}$ $I_F = 1\text{A}$, $dF/dt = -100\text{ A}/\mu\text{s}$, $V_r = -30\text{V}$
Q_{rr} Recovered charge	250	300	nC	$T_J = 25^\circ\text{C}$ $I_F = 1\text{A}$, $dF/dt = -100\text{ A}/\mu\text{s}$, $V_r = -30\text{V}$



Voltage ratings ($T_J = T_J \text{ max.}$)

Type number	V_{RM} : maximum repetitive peak reverse voltage	V_{RSU} : maximum non-repetitive peak reverse voltage	$I_{RM} \text{ Max}$ @ 100°C	$I_{RM} \text{ Max}$ @ 150°C	$I_{RM} \text{ Typ.}$ @ 25°C
	V	V	mA	mA	μA
60HFU(R)-100	100	110	5	15	50
60HFU(R)-200	200	220	5	15	50
60HFU(R)-300	300	330	5	15	50
60HFU(R)-400	400	440	5	15	50
60HFU(R)-500	500	550	5	25	50
60HFU(R)-600	600	660	5	25	50